

Fast Forward with In-Design Lithography DFM using DRC+ in Synopsys ICC / ICV

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- DFM Challenges to Lithography
- Conventional Approach to Litho DFM Design Flow
- Design Fast forward using DRC+ in In-Design Flow
- DRC+ ICV Pattern Matching: Detection and Fixing
- Conclusion



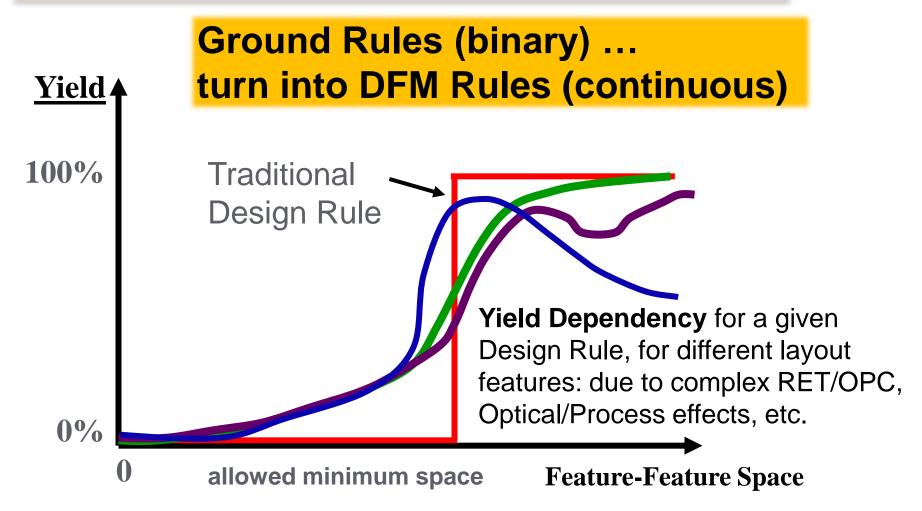


- DFM Challenges to Lithography
 - Physical Design Dependent Yield
 - More Rules, Increasing Complexity
- Conventional Approach to Litho DFM Design Flow
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DFM Challenges: 28nm and below Physical Design dependent Yield





Dr. Luigi Capodieci, Director of DFM, GLOBALFOUNDRIES, GTC 2010



DFM Challenges: 28nm and below Physical Design dependent Yield



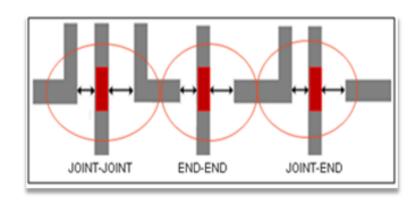
Configuration: tip-to-side **DRC** constraint ≥ 60 nm **DRC Plus DFM** constraint ≥ 80 nm DRC Plus Rule Deck



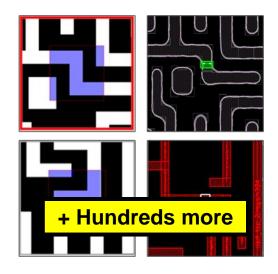
DFM Challenges: More Rules...



 Not all DFM critical layout patterns can easily and rightfully be translated into design rules.



Few DFM Critical patterns supported by Design Rules



Hundreds more DFM patterns needs to be supported



DFM Challenges: Increasing Complexity



- DFM routing rules: pessimistic and restrictive.
- Significant impact on routing runtime.

Placed Design		Routing		
Chip Area	0.041 mm ²	Classic PNR	DFM Enforced PNR	
Core Area	0.037 mm ² (192μm x 192μm)	Technology file Routing	Technology file Routing	
Std. Cell Density (Cell Utilization)	82.26%	Runtime 32 minutes	Runtime 60 minutes	
Instance Count	~ 25 K			



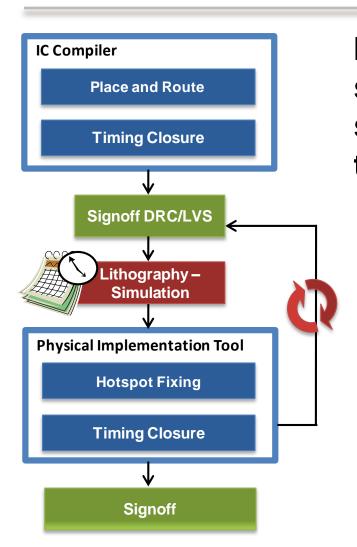


- DFM Challenges
- Conventional Approach to Litho DFM Design Flow
 - Implement then Verify
 - Model Based Lithography Simulation
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Conventional DFM Design Flow





Iterations due to DFM lithography simulations being done in late stage of design can result into tapeout delays

Design Iterations + Hours and Days of Model Based Lithography Simulation

Like digging a mountain until a rat comes out.



Conventional Design Flow Issues



- Late stage surprises: DFM Physical verification only at the end of design.
- GDS streaming-in and out
- Model Based Lithography Simulation
 - time consuming stage.
- Pushing all DFM into Design rules cannot support all your DFM needs.



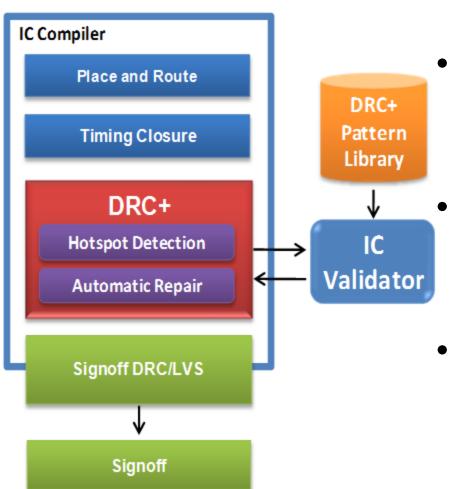


- DFM Challenges
- Conventional Approach to Litho DFM Design Flow
- Design Fast forward using DRC+ in In-Design Flow
 - Ultra-Fast DRC+ Pattern-Matching in IC Validator
 - Seamless Integration With IC Compiler
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DRC+ in Integrated Design Flow





- Use Ultra-Fast DRC+ Pattern-Matching in IC Validator
 - In-Design Automatic Fixing of Lithography Hotspots
- Address timing issues Immediately inside the design



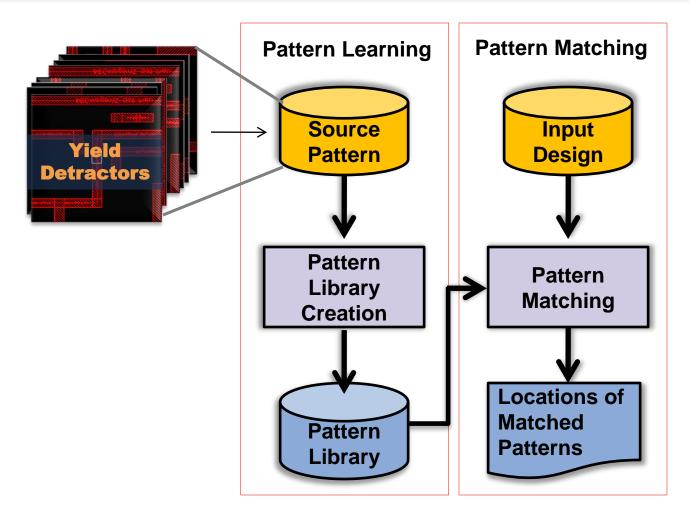


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DRC+ ICV Pattern Matching Flow





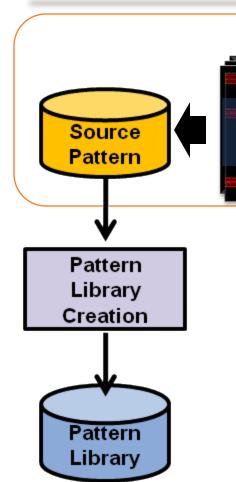


ICV Pattern Library Preparation

DRC +

Library





Collection of foundry silicon correlated DRC+ lithography problematic patterns.

Standard ICV Execution

```
% setenv PM_LIB_PATH .
% setenv PM_LIB_NAME PATTERN_LIB
% icv -vue \
    -f GDSII-i pattern.gds \
    -c TOP learn.rs
```



ICV Pattern Library Preparation Runset Overview



learn.rs

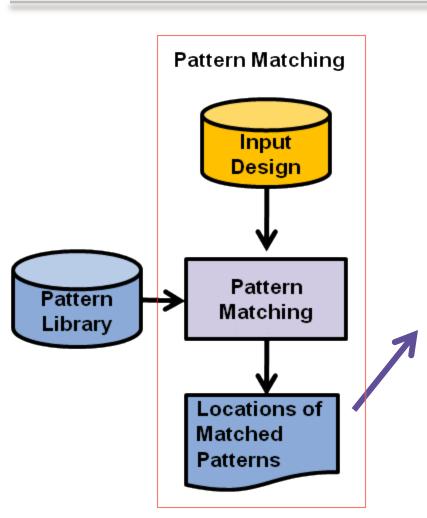
```
#define PM RS
#include <icv.rh>
// Synopsys, Inc. All rights reserved.
   Pattern Match Sample runset
User Defined Environment Variables
#pragma envvar default PM LIB PATH "."
#pragma envvar default PM LIB NAME "PATTERN LIB"
pattern options (
pattern_library_path = $PM_LIB_PATH
Pattern Database Specific
library (
  format = GDSII,
  library name = pattern.gds,
   cell = TOP
);
```

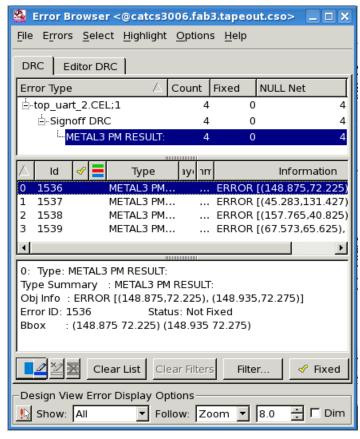
```
Layout Number
metal: polygon layer = assign (\{3,0\}\});
pattern marker: polygon layer = assign ( {{4,0}, {5,0} } );
pattern text id:text layer = assign text({{6,0}};
Pattern Library Learn
tmp violation @= {
@"UNMATCHED pattern marker";
pattern_learn (
pattern_library_layer = $PM_LIB_NAME,
pattern layers = {metal},
pattern marker = pattern marker,
pattern_text_id = pattern_text_id,
match\_ambit = \{x.xx,x.xx,x.xx,x.xx\},
pattern_fuzziness = PM_EDGE_UNIFORM,
uniform_fuzzy_size = x.xxx,
        );
```



DRC+ ICV Pattern Matching Flow









ICV Pattern Pattern Matching Runset Overview



match.rs

```
User Defined Environment Variables
                                                           metal layer list: list of polygon layer =
#pragma envvar default PM LIB PATH "/pat lib "
                                                            {MET1, MET2, MET3, MET4, MET5, MET6,
#pragma envvar default PM_LIB_NAME " PATTERN LIB"
                                                           MET7};
#pragma envvar default PM TOP MET "7"
                                                           Pattern Matching
pattern options (
pattern library path = $PM LIB PATH
                                                           for (i = 0 to strtoi (PM_TOP_MET)-1) {
Design Laver Numbers
                                                               layer_index : integer = i + 1;
                                                                tmp violation @= {@"M"+layer index: ";
MET1: polygon layer = assign (\{\{15,0\}\});
MET2: polygon layer = assign (\{\{17,0\}\});
                                                               pattern match (
MET3: polygon layer = assign (\{\{19,0\}\});
                                                                  pattern library layer = $PM LIB NAME,
MET4: polygon layer = assign (\{\{21,0\}\});
                                                                  pattern layers = {metal layer list[i]},);
MET5: polygon layer = assign (\{31,0\});
MET6: polygon layer = assign (\{44,0\}\});
MET7: polygon layer = assign (\{46,0\}\});
```

Standard ICV Execution





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Performance of DFM Verification: ICV Pattern Matching



Design Name	Α	В	С	D	Е	F	G	Н	
Chip Size (mm²)	0.024	0.033	0.240	0.309	0.464	0.027	0.036	0.032	
Core Size (mm ²)	0.023	0.031	0.115	0.294	0.440	0.026	0.035	0.030	
Std Cell Density	85%	68%	56%	95%	64%	76%	60%	93%	
Instance Count	18K	18.5K	83.5K	294K	303K	13.5K	14K	34K	
DRC+ ICV Hotspots	14	8	35	199	133	1	1	11	
Found Normalized Hotspots	605	259	306	678	302	39	29	363	
Found to	322 Lithography Hotspots / mm²								

- Consists of Design such as CPU and JPEG.
- Designs routed with different levels of design complexity.



Performance of DFM Verification: ICV Pattern Matching

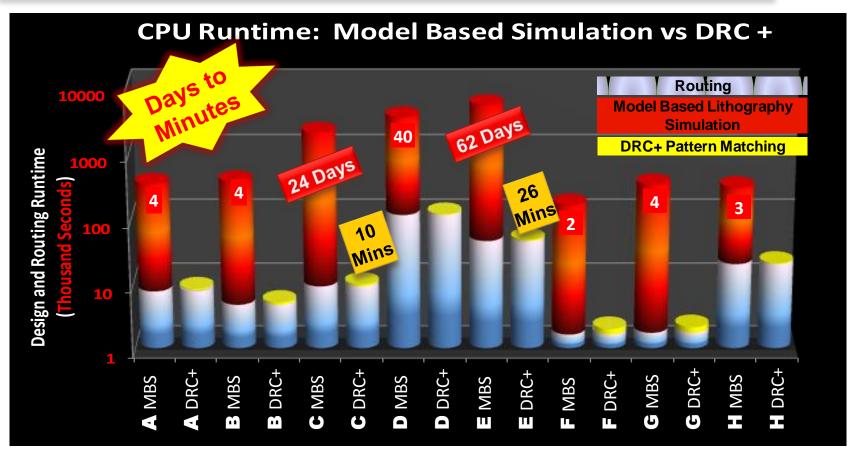


Design Name	Α	В	С	D	Е	F	G	Н
DRC+ ICV Hotspots Found	14	8	35	199	133	1	1	11
Runtime: Multi-threading (8 threads) (minutes)	1.17	0.72	1.22	6.52	3.22	0.62	0.67	1.17
Runtime: Normalized to 1 thread (minutes)	9	6	10	52	26	5	5	9
Peak Memory (Mb)	71	55	102	314	324	38	37	80
Memory Usage (Mb)	248	248	248	248	247	248	247	247



Performance of DFM Verification: Printability Simulation vs. DRC+





- DRC+ is over 10,000 times faster than printability simulation
- DRC+ detection and fixing adds very little to the overall routing runtime



Performance of ICC In-Design Pattern Matching and Fixing



Design Name		1	J	K	
Chip Size (mm²)		0.594	0.340	0.594	
Core Size (mm²)		0.505	0.263	0.505	
Std Cell Density		73.41%	77%	73.41%	
Instance Count		364K	16K	364K	
DRC+ ICV Hotspots Found		15	4	1335	
	1	0	0	244	
Autofix Iteration	2	-	-	163	
Remaining Error	3	-	=	83	
	4	=	=	83	
DRC+ ICV Detection Fixing Runtime (seconds)		180	145	4800	



DRC+ In-Design Pattern Matching Commands



Setting Up the Physical Sign-Off Options

```
icc_shell> set_physical_signoff_options \
    -exec_cmd icv \
    -drc_runset match.rs
```

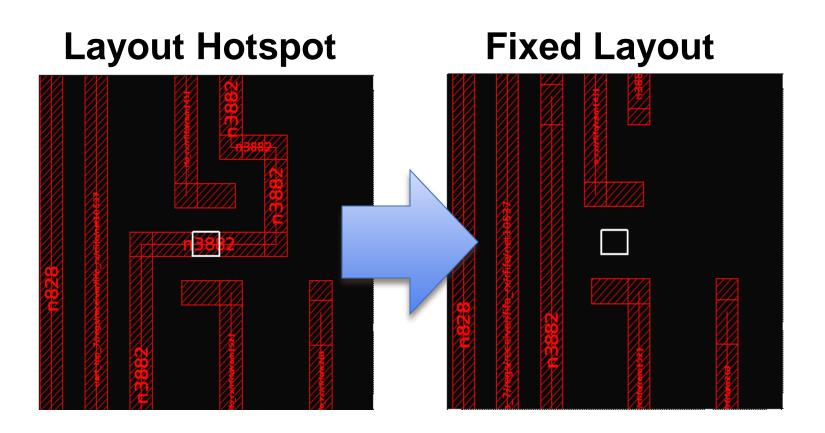
Running Pattern-Matching for Hotspot Detection

Automatically Fixing Hotspot Patterns



DRC+ Auto-fixing Results:1

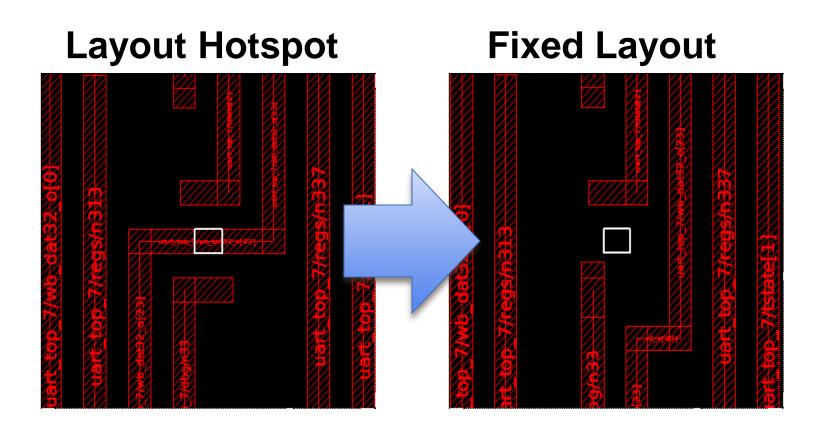






DRC+ Auto-fixing Results:2

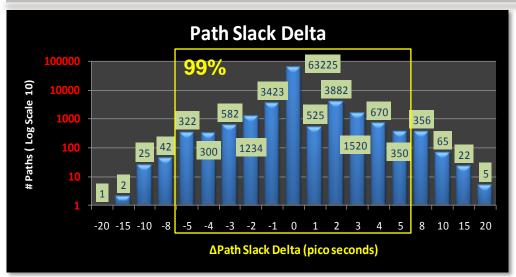


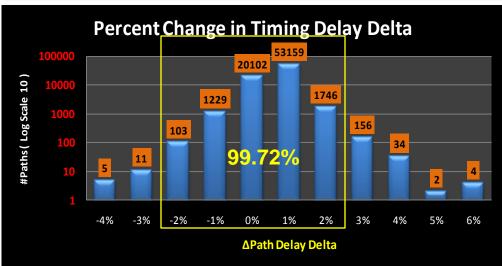




Timing Impact Analysis Results:







Design analyzed is with 1252 of 1335 hotspots violations fixed inside ICC with 4 Iterations.

- high fixing rate of 94% at 4th iteration with minimal timing impact.
- 99% of timing paths has timing delta of only ±5ps.
- 99.72% of the slack paths that changed have path slack changes of ± 2%.





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Conclusion



- DRC+
 - 28nm library of yield-critical patterns
 Industry first from GLOBALFOUNDRIES
- At 28nm and below, DFM is required for yield
- DRC+ in IN-DESIGN ICC/ICV
 - ICV PM 10,000 times faster than printability simulation
 - DFM physical verification integrated in the timing closure loop
 - Router Integrated Hotspots Detection and Fixing.
 - Ultra fast pattern matching engine minimizes cost to router runtime.



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Thank You!

Now Your Time Q&A Session

